High Speed Switching Silicon N-channel MOSFET

AEC-Q101 COMPLIANCE

DESCRIPTION

INK0012AM1 is a Silicon N-channel MOSFET.

This product is most suitable for use such as portable machinery, because of low voltage drive and low on resistance.

FEATURE

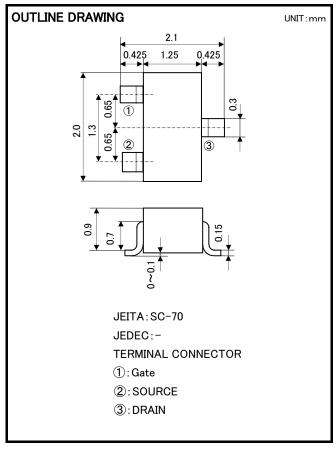
- •Input impedance is high, and not necessary to consider a drive electric current.
- •Drive voltage 4V
- ·Low on Resistance.

RDS(ON)=1.7 Ω (TYP) @ID=100mA, VGS=4.0V RDS(ON)=1.0 Ω (TYP) @ID=100mA, VGS=10V

- ·High speed switching.
- ·Small package for easy mounting.

APPLICATION

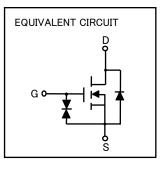
High speed switching, Analog switching

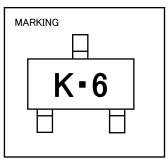


MAXIMUM RATING(Ta=25°C)

SYMBOL	PARAMETER	RATING	UNIT
VDSS	Drain-source voltage	30	V
VGSS	Gate-source voltage	±20	٧
ID	Drain current(DC)	200	mA
IDP	Drain current(Pulse) ※1	400	mA
PD	Total power dissipation	200	mW
Tch	Channel temperature	+150	°C
Tstg	Range of Storage temperature	−55 ~ +150	°C

 $\times 1: Pw \le 10 \,\mu$ s, Duty cycle $\le 1\%$



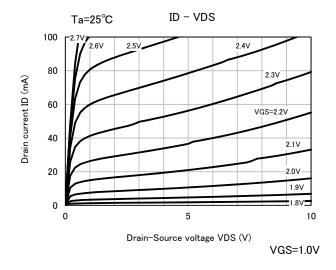


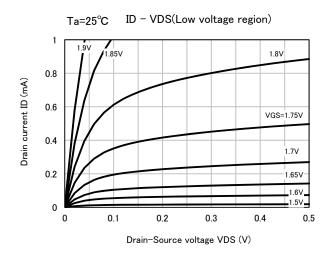
ELECTRICAL CHARACTERISTICS (Ta=25°C)

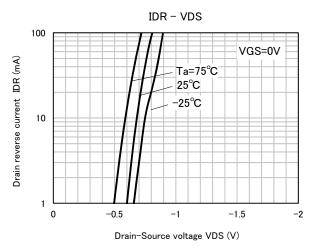
DADAMETED	SYMBOL	TEST CONDITION	LIMIT			LINUT
PARAMETER			MIN	TYP	MAX	UNIT
Drain-source breakdown voltage	V(BR)DSS	$I_{D}=100 \mu$ A, $V_{GS}=0V$	30	-	-	V
Gate-source leak current	Igss	$V_{GS}=\pm 15V, V_{DS}=0V$	_	-	±1.0	μΑ
Zero gate voltage drain current	IDSS	V _{DS} =30V, V _{GS} =0V	_	_	1.0	μΑ
Gate threshold voltage	Vth	$I_D=250 \mu A, V_{DS}=V_{GS}$	1.0	-	2.0	V
Forward transfer admittance	Yfs	V _{DS} =10V, I _D =100mA	_	245	_	mS
Static drain-source on-state resistance	Pro(on)	I _D =100mA, V _{GS} =4.0V	_	1.7	_	Ω
Static drain-source on-state resistance	ce RDS(ON)	I _D =100mA, V _{GS} =10V	_	1.0	_	
Input capacitance Ciss		\/ -10\/ \/ -0\/ [- 1M] -	_	23	_	pF
Output capacitance	Coss	V_{DS} =10V, V_{GS} =0V, f=1MHz	_	7.0	-	pF
Contact in a time	ton	V_{DD} =5V, I_{D} =10mA	-	30	_	ns
Switching time	toff	V _{GS} =0∼5V	_	66	-	ns

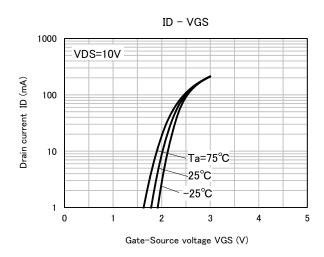
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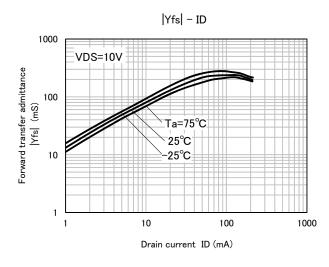
TYPICAL CHARACTERISTICS

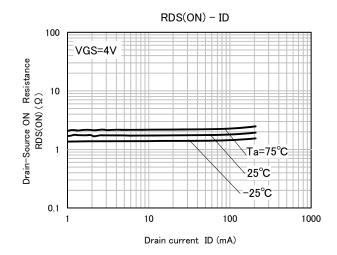




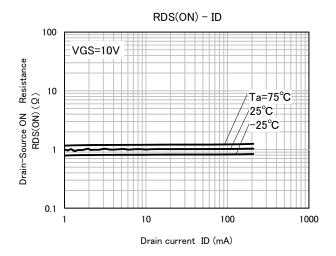


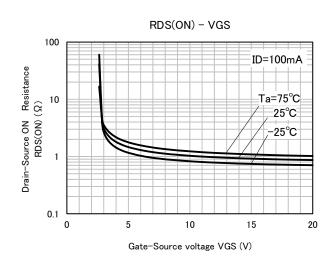


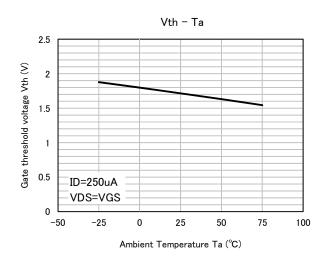


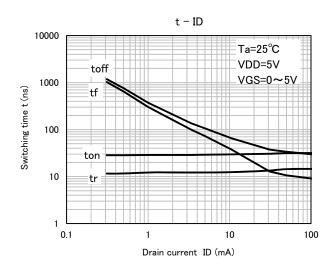


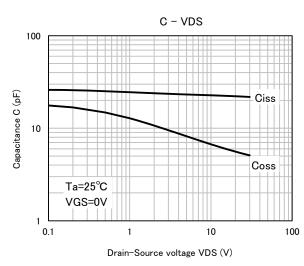
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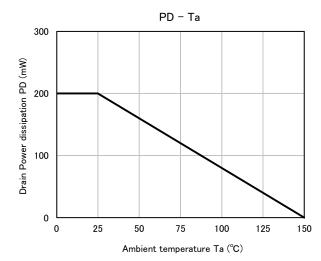






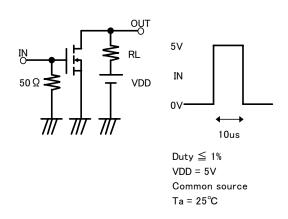


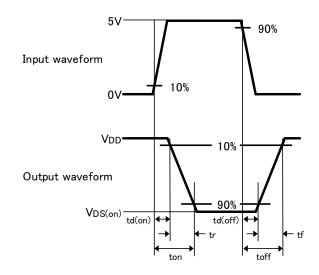




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Switching time test condition







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